1-7. (Cancelled).

8. (Currently Amended) A method of forming a dynamic random access memory structure, said method comprising:
forming a trench within a substrate;
filling said trench with a trench conductor;
forming a pad oxide along a surface of said substrate adjacent said trench;
forming a collar along an upper portion of said trench such that said collar insulates said substrate from said trench conductor;
recessing said collar and said pad oxide;
depositing a lip strap over said trench conductor and in recesses produced by said recessing, wherein said recessing allows a portion of said collar to remain in contact with the adjacent wall of said trench such that said collar separates said lip strap from said adjacent wall of said trench; and
forming an isolation region adjacent said lip strap.

9. (Original) The method in claim 8, further comprising forming a control device adjacent said trench, wherein said trench has a corner adjacent said control device and said lip strap comprises a conductor surrounding said corner.

10. (Previously Presented) The method in claim 9, wherein said forming of said control device includes forming a control device conductive region adjacent said trench and said lip strap comprises a conductor formed along a side of said trench and along a portion of said control device conductive region.

11. (Original) The method in claim 8, further comprising forming a collar insulator along a top portion of said trench, wherein said lip strap comprises a conductor formed to extend from a top of said collar to a top of said trench, said lip strap further extending along a surface of said device adjacent said trench and perpendicular to said trench.

12. (Original) The method in claim 11, further comprising lining said trench with a node dielectric, wherein said lip strap surrounds an upper portion of said node dielectric adjacent said top portion of said trench.

13. (Original) The method in claim 8, further comprising forming a trench top oxide, such that said lip strap extends into said trench top oxide and forms an inverted U-shaped structure.

14. (Original) The method in claim 8, wherein said lip strap comprises a conductor formed along two perpendicular portions of a top corner of said trench.

15. (Currently Amended) A method of forming a dynamic random access memory structure, said method comprising:
forming a trench within a substrate;
filling said trench with a trench conductor;
forming a pad oxide along a surface of said substrate adjacent said trench;
forming a collar along an upper portion of said trench such that said collar insulates said substrate from said trench conductor;
forming an isolation region adjacent said trench conductor;
recessing said collar and said pad oxide; and
depositing a lip strap over said trench conductor and in recesses produced by said recessing, wherein said recessing allows a portion of said collar to remain in contact with the adjacent wall of said trench such that said collar separates said lip strap from said adjacent wall of said trench.

16. (Original) The method in claim 15, further comprising forming a control device adjacent said trench, wherein said trench has a corner adjacent said control device and said lip strap comprises a conductor surrounding said corner.

17. (Previously Presented) The method in claim 16, wherein said forming of said control device includes forming a control device conductive region adjacent said trench

and said lip strap comprises a conductor formed along a side of said trench and along a portion of said control device conductive region.

18. (Original) The method in claim 15, further comprising forming a collar insulator along a top portion of said trench, wherein said lip strap comprises a conductor formed to extend from a top of said collar to a top of said trench, said lip strap further extending along a surface of said device adjacent said trench and perpendicular to said trench.

19. (Previously Presented) The method in claim 15, further comprising lining said trench with a node dielectric, wherein said lip strap surrounds an upper portion of said node dielectric adjacent said top portion of said trench.

20. (Original) The method in claim 15, further comprising forming a trench top oxide, such that said lip strap extends into said trench top oxide and forms an inverted U-shaped structure.

21. (Currently Amended) A method of forming a dynamic random access memory structure, said method comprising:
forming a trench within a substrate;
filling said trench with a trench conductor;
forming a pad oxide along a surface of said substrate adjacent said trench;
forming a collar along an upper portion of said trench such that said collar insulates said substrate from said trench conductor;
recessing said collar and said pad oxide; and
depositing a lip strap over said trench conductor and in recesses produced by said recessing, wherein said recessing allows [a portion of] said collar to remain in contact with the adjacent wall of said trench such that said collar separates said lip strap from said adjacent wall of said trench; [and
forming an isolation region adjacent said lip strap].

22. (Previously Presented) The method in claim 21, further comprising forming a control device adjacent said trench, wherein said trench has a corner adjacent said control device and said lip strap comprises a conductor surrounding said corner.

23. (Previously Presented) The method in claim 22, wherein said forming of said control device includes forming a control device conductive region adjacent said trench and said lip strap comprises a conductor formed along a side of said trench and along a portion of said control device conductive region.

24. (Previously Presented) The method in claim 21, further comprising forming a collar insulator along a top portion of said trench, wherein said lip strap comprises a conductor formed to extend from a top of said collar to a top of said trench, said lip strap further extending along a surface of said device adjacent said trench and perpendicular to said trench.

25. (Previously Presented) The method in claim 24, further comprising lining said trench with a node dielectric, wherein said lip strap surrounds an upper portion of said node dielectric adjacent said top portion of said trench.

26. (Previously Presented) The method in claim 21, further comprising forming a trench top oxide, such that said lip strap extends into said trench top oxide and forms an inverted U-shaped structure.

27. (Previously Presented) The method in claim 21, wherein said lip strap comprises a conductor formed along two perpendicular portions of a top corner of said trench.